L Number	Hits	Search Text	DB	Time stamp
1	1	5939886.pn.	USPAT; US-PGPUB	2002/09/18 15:04
2	1	5939886.pn.	USPAT;	2002/09/18
	0	("1 and (voltage or volt)").PN.	US-PGPUB USPAT;	15:04 2002/09/10
_	١	(I and (voitage of voit)).in.	US-PGPUB	10:12
_	93	156/345.28.ccls.	USPAT; US-PGPUB	2002/09/10
_	76	156/345.28.ccls. and (voltage or volt)	USPAT; US-PGPUB	2002/09/10 10:38
_	41	(156/345.28.ccls. and (voltage or volt))	USPAT; US-PGPUB	2002/09/10 11:12
	17	<pre>and ((substrate or wafer) with voltage) ((156/345.28.ccls. and (voltage or volt))</pre>	USPAT;	2002/09/10
	1,	and ((substrate or wafer) with voltage)) and impedance	US-PGPUB	11:12
-	28	((156/345.28, 345.24, 345.13,	USPAT;	2002/09/11
		345.15).ccls. and (substrate or wafer) with voltage) not ((156/345.28).CCLS.)	US-PGPUB	08:58
-	466	h011021/\$.ipc. and ((substrate or wafer)	USPAT;	2002/09/11
	150	with voltage) and impedance c23c016/\$.ipc. and ((substrate or wafer)	US-PGPUB USPAT;	12:14
-	153	with voltage) and impedance	US-PGPUB	13:00
_	24	(118/712).ccls. and (substrate or wafer)	USPAT;	2002/09/11
	5	with voltage (118/712).ccls. and ((substrate or wafer)	US-PGPUB USPAT;	2002/09/10
-		with voltage) and impedance	US-PGPUB	12:58
-	607	(h011021/\$.ipc. and ((substrate or wafer)	USPAT; US-PGPUB	2002/09/10
		<pre>with voltage) and impedance) or (c23c016/\$.ipc. and ((substrate or wafer)</pre>	U3-FGFUB	12.33
_	13	with voltage) and impedance) c23c016/\$.ipc and ((substrate or wafer)	JPO;	2002/09/10
		with voltage) and impedance	DERWENT	13:00
-	102	h011021/\$.ipc. and ((substrate or wafer)	JPO; DERWENT	2002/09/10 13:01
_	105	<pre>with voltage) and impedance (c23c016/\$.ipc. and ((substrate or wafer)</pre>	JPO;	2002/09/10
. 47		with voltage) and impedance) or	DERWENT	14:19
		(h011021/\$.ipc. and ((substrate or wafer) with voltage) and impedance)		
-	4170	(substrate or wafer or work) and plasma	USPAT;	2002/09/10
	1.674	and voltage and current and impedance ((substrate or wafer or work) and plasma	US-PGPUB USPAT;	18:30 2002/09/10
-	1674	and voltage and current and impedance)	US-PGPUB	14:27
		and (vacuum or exhaust) and semiconductor		2002/00/10
-	93	(156/345.28).CCLS.	USPAT; US-PGPUB	2002/09/10 19:07
_	237	((substrate or wafer or work) with	USPAT;	2002/09/10
		voltage) and current and impedance and semiconductor and vacuum and probe	US-PGPUB	19:11
	6	(("5198072") or ("5444259") or	USPAT;	2002/09/11
		("5472561") or ("5576629") or ("5711843")	US-PGPUB	08:50
_	69	or ("5830310")).PN. (156/345.28, 345.24, 345.13,	USPAT;	2002/09/11
		345.15).ccls. and (substrate or wafer)	US-PGPUB	10:41
	21	with voltage (substrate or wafer) with (rear or back	USPAT;	2002/09/11
-	31	(substrate or water) with (rear of back adj side) with voltage and probe	US-PGPUB	11:22
-	72	(118/712).ccls. and (substrate or wafer)	USPAT;	2002/09/11
	27012	same (Film adj thickness)	US-PGPUB USPAT;	12:13 2002/09/11
-	27912	iii (aCiii.as.	US-PGPUB	12:13
-	427	hitachi.as. and ((substrate or wafer)	USPAT;	2002/09/11
		with voltage) and impedance	US-PGPUB	12:15